

# PRESS RELEASE

JUN 15, 2020

## Bruckewell Announces the super junction high voltage MOSFET Series

It is new generation of super junction (SJ) trench semiconductor technology for high-efficient MOSFETs. The devices based on the new process operate with lower EMI noise and reduced on resistance ( $R_{DS(ON)}$ ) compared to previous.

Applications

Power Charger

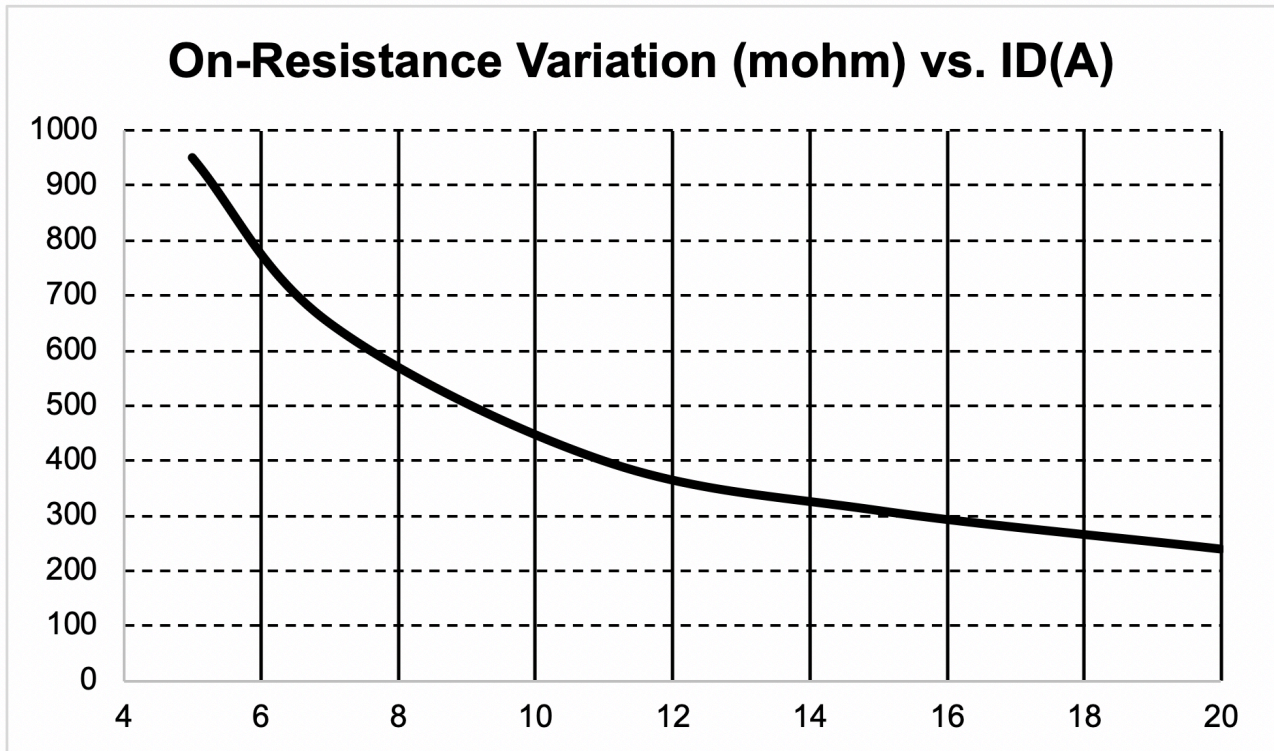
Date centers (Server power supplies, etc.)

Power conditioners for photovoltaic generators

Uninterruptible power systems

BW Part No.	Package	BVDSS (V)	ID (A)	$R_{DS(ON)}$ (m $\Omega$ ) Max. @10V	Qg(nC) Typ.	Ciss(pF) Typ.
MSP650N240	TO-220	650	20	240	38	1197
MSF650N240	TO-220F	650	20	240	38	1197
MSP650N420	TO-220	650	11	420	23	632
MSF650N420	TO-220F	650	11	420	23	632
MSD650N420	TO-252AA	650	11	420	23	632
MSP650N700	TO-220	650	7	700	16	423
MSF650N700	TO-220F	650	7	700	16	423
MSD650N700	TO-252AA	650	7	700	16	423
MSP800N500	TO-220	800	11	500	38	680
MSF800N500	TO-220F	800	11	500	38	680
MSD800N500	TO-252AA	800	11	500	38	680

## 650V Super Junction MOSFET RDS(on) Characteristic



**For the detail information and samples,**

**please contact our local sales representative or send to:  
[sales@bruckewell.com](mailto:sales@bruckewell.com)**

- **About Bruckewell Technology**

Since 2008, Bruckewell technology is a multinational discrete semiconductor design company with headquarters in Hsinchu, Taiwan.

Bruckewell offers the KGD wafers, power semiconductor devices by applying both silicon and wide bandgap (WBG) materials such as SiC JBS Diode and Field Stop IGBT power devices and design in projects. Bruckewell also owns patents for the Schottky Barrier Diode, Silicon Device, Special trench MOSFET.

Bruckewell dedicate to contribute its power semiconductor technology and solution on the Electronics, Industrial and Automotive application.